

Product	Ultra Fast Rectifier Diodes	Type	8GHESV420-1000								
Metallization	<p>Top Al ①</p> <p>Bottom Ag ②</p>										
Dimension in mils	<table border="1"> <thead> <tr> <th></th> <th>Dimension</th> </tr> </thead> <tbody> <tr> <td>A</td> <td>166±2</td> </tr> <tr> <td>B</td> <td>133(min.)</td> </tr> <tr> <td>D</td> <td>12±1.0</td> </tr> <tr> <td>E</td> <td>2(max.)</td> </tr> </tbody> </table>				Dimension	A	166±2	B	133(min.)	D	12±1.0
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Absolute Maximum Ratings (Ta=25°C)

PEAK REVERSE VOLTAGE VRRM .. 1000 V
FORWARD SURGE CURRENT IFSM.... 300 A
STORAGE TEMPERATURE RANGE Tstg .. -65~150°C

Electrical Characteristics

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE(for cell type)	VF	IF=20A	1.70 V (MAX)
REVERSE CURRENT	IR	VR=1000V	10µA (MAX)
REVERSE RECOVERY TIME	TRR	RG1	75ns
BREAKDOWN VOLTAGE	BVR	IR=10µA	1050V (MIN)

Dice Yield Assurance : 95%